





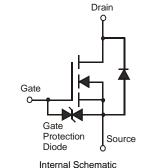
N-CHANNEL ENHANCEMENT MODE MOSFET

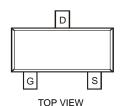
Features

- Low On-Resistance
 - $25m\Omega$ @ $V_{GS} = 4.5V$
 - $29m\Omega$ @ $V_{GS} = 2.5V$
 - $36m\Omega$ @ $V_{GS} = 1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected Up To 2kV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)









TOP VIEW

Maximum Ratings @T_A = 25°C unless otherwise specified

Charact	eristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	20	V	
Gate-Source Voltage		V _{GSS}	±12	V	
Continuous Drain Current (Note 3)	Steady State	T _A = 25°C T _A = 70°C	I _D	6.5 5.2	А
Pulsed Drain Current			I _{DM}	30	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	0.81	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{0JA}	157	°C/W
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on FR-4 PCB with minimum recommended pad layout.

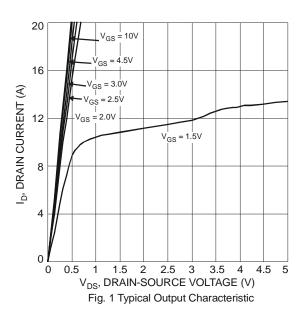


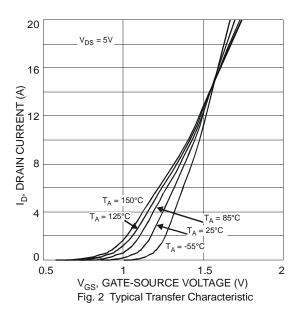
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)								
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	_	_	1.0	μА	$V_{DS} = 20V, V_{GS} = 0V$		
Gate-Source Leakage	I_{GSS}	_		±10	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$		
Gate-Source Breakdown Voltage	BV _{SGS}	±12	-	1	V	$V_{DS} = 0V, I_{G} = \pm 250 \mu A$		
ON CHARACTERISTICS (Note 4)								
Gate Threshold Voltage	$V_{GS(th)}$	0.5	_	0.9	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$		
			21	25	mΩ	$V_{GS} = 4.5V, I_D = 6.5A$		
Static Drain-Source On-Resistance	R _{DS (ON)}	_	23	29		$V_{GS} = 2.5V, I_D = 5.5A$		
			28	36		$V_{GS} = 1.8V, I_D = 3.5A$		
Forward Transfer Admittance	Y _{fs}	_	8	_	S	$V_{DS} = 10V, I_{D} = 5A$		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{iss}	_	151	_	pF	101/1/		
Output Capacitance	Coss	_	91		рF	$V_{DS} = 10V, V_{GS} = 0V$ -f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	32		pF	71 = 1.01VIDZ		
Total Gate Charge	Q_g	_	8.5	_	nC			
Gate-Source Charge	Q _{gs}	_	1.6	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5A$		
Gate-Drain Charge	Q_{gd}	_	2.8	_	nC			
Turn-On Delay Time	t _{D(on)}	_	54		ns			
Turn-On Rise Time	t _r	_	66		ns	$V_{DD} = 10V, V_{GS} = 4.5V,$		
Turn-Off Delay Time	t _{D(off)}	_	613	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$, $I_D = 1A$		
Turn-Off Fall Time	t _f	_	205		ns			

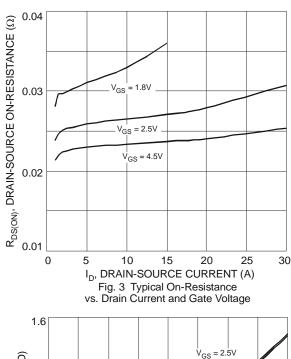
Notes:

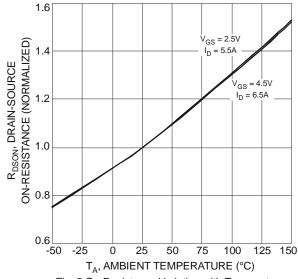
4. Short duration pulse test used to minimize self-heating effect.











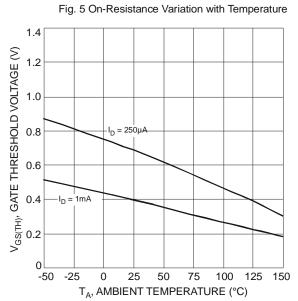


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

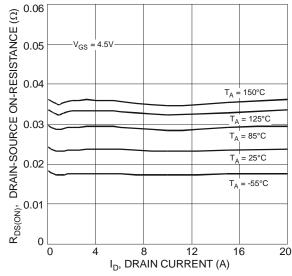


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

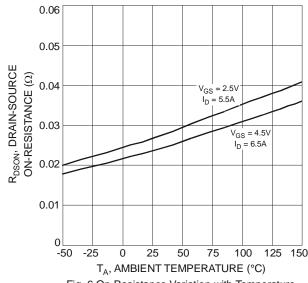


Fig. 6 On-Resistance Variation with Temperature

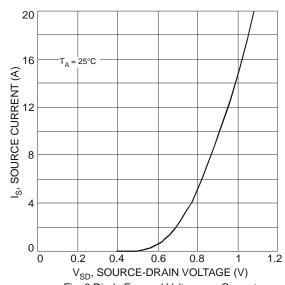
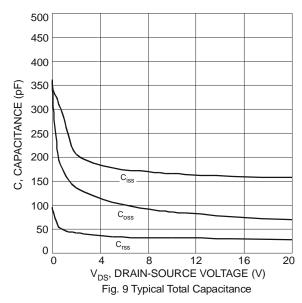


Fig. 8 Diode Forward Voltage vs. Current





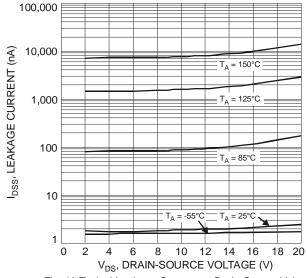
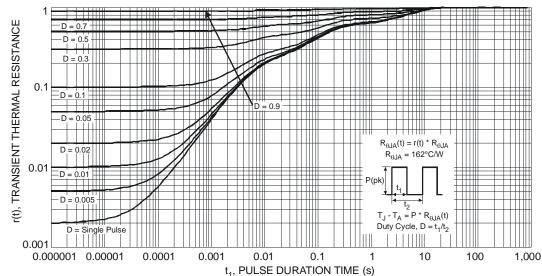


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage



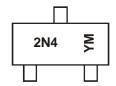
Ordering Information (Note 5)

Part Number	Case	Packaging
DMG6968U-7	SOT-23	3000/Tape & Reel

Fig. 11 Transient Thermal Response

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



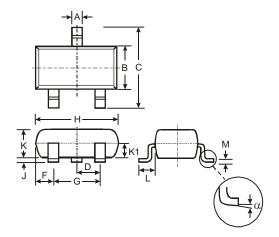
2N4 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2009	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ	2	7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

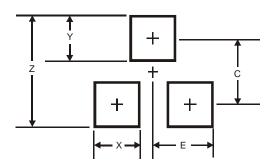


Package Outline Dimensions



	SOT-23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	1	0.400			
L	0.45	0.61	0.55			
M	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
С	2.0
F	1.35



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